

PS9505,PS9505L1,PS9505L2,PS9505L3

R08DS0015EJ0100 Rev.1.00 Jan 06, 2012

2.5 A OUTPUT CURRENT, HIGH CMR, IGBT GATE DRIVE, 8-PIN DIP PHOTOCOUPLER

DESCRIPTION

The PS9505, PS9505L1, PS9505L2 and PS9505L3 are optically coupled isolators containing a GaAlAs LED on the input side and a photo diode, a signal processing circuit and a power output transistor on the output side on one chip.

The PS9505 Series is designed specifically for high common mode transient immunity (CMR), high output current and high switching speed.

The PS9505 Series is suitable for driving IGBTs and MOS FETs.

The PS9505 Series is in a plastic DIP (Dual In-line Package).

The PS9505L1 is lead bending type for long creepage distance.

The PS9505L2 is lead bending type for long creepage distance (Gull-wing) for surface mount.

The PS9505L3 is lead bending type (Gull-wing) for surface mounting.

FEATURES

- Long creepage distance (8 mm MIN.: PS9505L1, PS9505L2)
- Large peak output current (2.5 A MAX., 2.0 A MIN.)
- High speed switching (tplh, tphL = 0.25 μ s MAX.)
- · UVLO (Under Voltage Lock Out) protection with hysteresis
- High common mode transient immunity (CMH, CML = $\pm 25 \text{ kV}/\mu \text{s MIN.}$)
- Embossed tape product: PS9505L2-E3: 1 000 pcs/reel

: PS9505L3-E3: 1 000 pcs/reel

<R> <R> · Pb-Free product

· Safety standards

• UL approved: No. E72422

CSA approved: No. CA 101391 (CA5A, CAN/CSA-C22.2 60065, 60950)

· SEMKO approved: No. 1115598

DIN EN60747-5-2 (VDE0884 Part2) approved: No. 40024069 (Option)

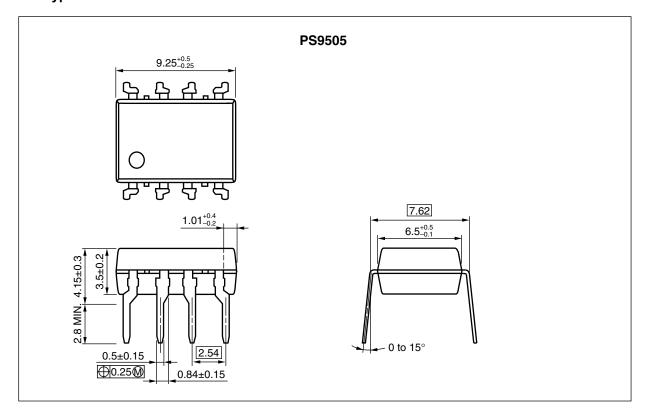
PIN CONNECTION (Top View) 1. NC 2. Anode 3. Cathode 4. NC 5. Vee 6. Vo 7. Vo 8. Vcc

APPLICATIONS

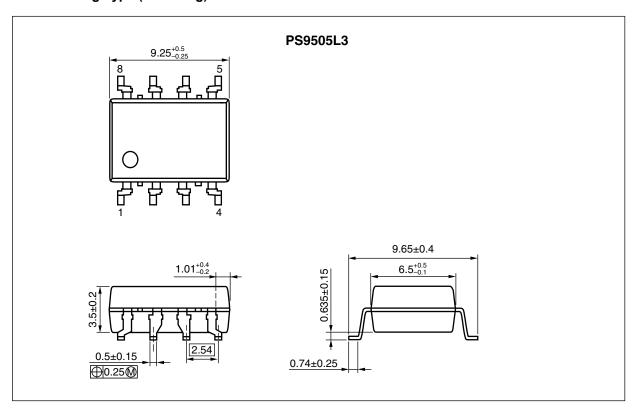
- · IGBT, Power MOS FET Gate Driver
- Industrial inverter
- · IH (Induction Heating)

PACKAGE DIMENSIONS (UNIT: mm)

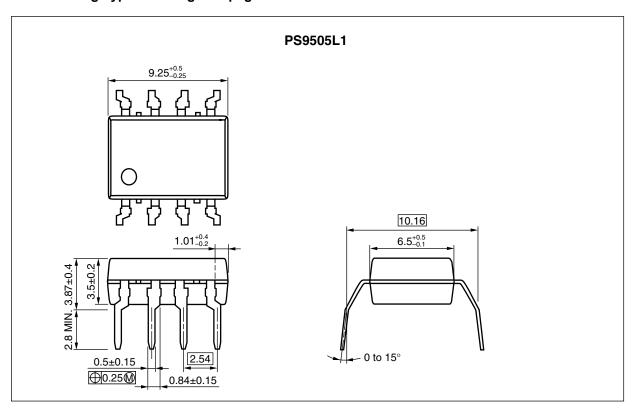
DIP Type



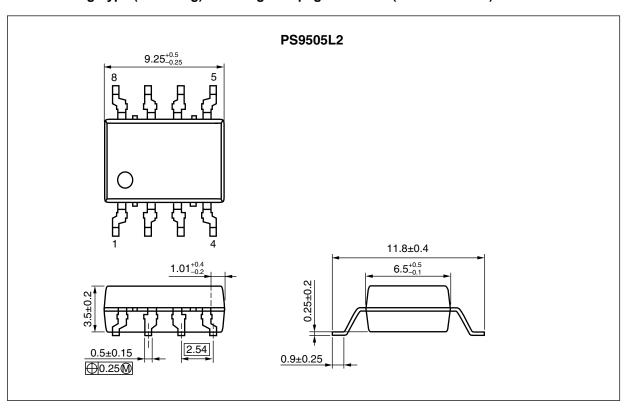
Lead Bending Type (Gull-wing) For Surface Mount



Lead Bending Type For Long Creepage Distance



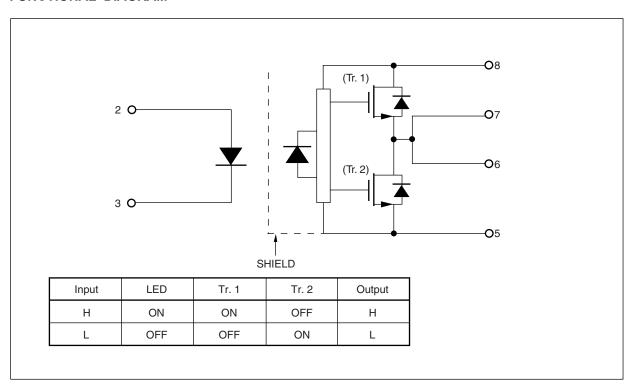
Lead Bending Type (Gull-wing) For Long Creepage Distance (Surface Mount)



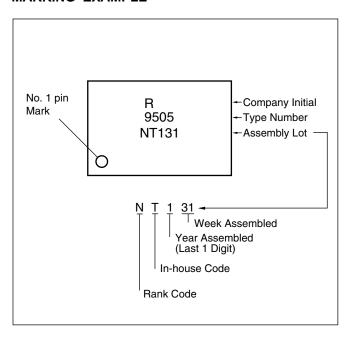
PHOTOCOUPLER CONSTRUCTION

Parameter	PS9505, PS9505L3	PS9505L1, PS9505L2
Air Distance (MIN.)	7 mm	8 mm
Outer Creepage Distance (MIN.)	7 mm	8 mm
Isolation Distance (MIN.)	0.4 mm	0.4 mm

FUNCTIONAL DIAGRAM



<R> MARKING EXAMPLE



<R> ORDERING INFORMATION

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number*1
PS9505	PS9505-AX	Pb-Free	50 Magazine Cases	Standard	PS9505
PS9505L1	PS9505L1-AX	(Ni/Pd/Au)		products	PS9505L1
PS9505L2	PS9505L2-AX			(UL, CSA, SEMKO	PS9505L2
PS9505L3	PS9505L3-AX			approved)	PS9505L3
PS9505L2-E3	PS9505L2-E3-AX		Embossed Tape		PS9505L2
PS9505L3-E3	PS9505L3-E3-AX		1 000 pcs/reel		PS9505L3
PS9505-V	PS9505-V-AX		50 Magazine Cases	DIN EN60747-5-2	PS9505
PS9505L1-V	PS9505L1-V-AX			(VDE0884 Part2)	PS9505L1
PS9505L2-V	PS9505L2-V-AX			approved	PS9505L2
PS9505L3-V	PS9505L3-V-AX			(Option)	PS9505L3
PS9505L2-V-E3	PS9505L2-V-E3-AX		Embossed Tape		PS9505L2
PS9505L3-V-E3	PS9505L3-V-E3-AX		1 000 pcs/reel		PS9505L3

^{*1} For the application of the Safety Standard, following part number should be used.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, unless otherwise specified)

	Parameter	Symbol	Ratings	Unit
Diode	Forward Current	lF	25	mA
	Peak Transient Forward Current (Pulse Width < 1 μ s)	If (TRAN)	1.0	А
	Reverse Voltage	VR	5	٧
Detector	High Level Peak Output Current *1	OH (PEAK)	2.5	А
	Low Level Peak Output Current ^{*1}	OL (PEAK)	2.5	Α
	Supply Voltage	(Vcc - Vee)	0 to 35	٧
Output Voltage		Vo	0 to Vcc	٧
	Power Dissipation *2	Pc	250	mW
Isolation Voltage*3		BV	5 000	Vr.m.s.
Total Power Dissipation *4		Рт	300	mW
Operating Frequency*5		f	50	kHz
Operating Ambient Temperature		TA	-40 to +110	°C
Storage ⁻	Temperature	Tstg	-55 to +125	°C

^{*1} Maximum pulse width = 10 μ s, Maximum duty cycle = 0.2%

^{*2} Reduced to 4.8 mW/°C at $T_A = 70$ °C or more.

^{*3} AC voltage for 1 minute at T_A = 25°C, RH = 60% between input and output. Pins 1-4 shorted together, 5-8 shorted together.

^{*4} Reduced to 5.4 mW/ $^{\circ}$ C at T_A = 70 $^{\circ}$ C or more.

^{*5} IOH (PEAK) \leq 2.0 A (\leq 0.3 μ s), IOL (PEAK) \leq 2.0 A (\leq 0.3 μ s)

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	(Vcc - Vee)	15		30	V
Forward Current (ON)	IF (ON)	7	10	16	mA
Forward Voltage (OFF)	V _F (OFF)	-2		0.8	٧
Operating Ambient Temperature	TA	-40		110	°C

<R> ELECTRICAL CHARACTERISTICS

(VEE = GND, unless otherwise specified and refer to RECOMMENDED OPERATING CONDITIONS)

	Parameter	Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit
Diode	Forward Voltage	VF	I _F = 10 mA, T _A = 25°C	1.2	1.56	1.8	٧
	Reverse Current	IR	V _R = 3 V, T _A = 25°C			10	μA
	Input Capacitance	Cin	f = 1 MHz, V _F = 0 V, T _A = 25°C		30		pF
Detector	High Level Output Current	Іон	Vo = (Vcc - 4 V)*2	0.5	2.0		Α
			Vo = (Vcc - 15 V)*3	2.0			
	Low Level Output Current	lou	Vo = (VEE + 2.5 V)*2	0.5	2.0		Α
			Vo = (VEE + 15 V)*3	2.0			
	High Level Output Voltage	Vон	Io = -100 mA*4	Vcc - 3.0	Vcc - 1.5		V
	Low Level Output Voltage	Vol	Io = 100 mA		0.1	0.5	٧
	High Level Supply Current	Іссн	Vo = open, I _F = 10 mA		1.4	3.0	mA
	Low Level Supply Current	Iccl	Vo = open, V _F = 0 to +0.8 V		1.3	3.0	mA
	UVLO Threshold	Vuvlo+	Vo > 5 V, I _F = 10 mA	10.8	12.3	13.4	٧
		Vuvlo-		9.5	11.0	12.5	
	UVLO Hysteresis	UVLO _{HYS}	Vo > 5 V, I _F = 10 mA	0.4	1.3		V
Coupled	Threshold Input Current $(L \rightarrow H)$	lflh	Io = 0 mA, Vo > 5 V		2.0	5.0	mA
	Threshold Input Voltage $(H \rightarrow L)$	V _{FHL}	Io = 0 mA, Vo < 5 V	0.8			V

^{*1} Typical values at T_A = 25°C.

^{*2} Maximum pulse width = 50 μ s, Maximum duty cycle = 0.5%.

^{*3} Maximum pulse width = 10 μ s, Maximum duty cycle = 0.2%

^{*4} VoH is measured with the DC load current in this testing (Maximum pulse width = 2 ms, Maximum duty cycle = 20%).

<R> SWITCHING CHARACTERISTICS

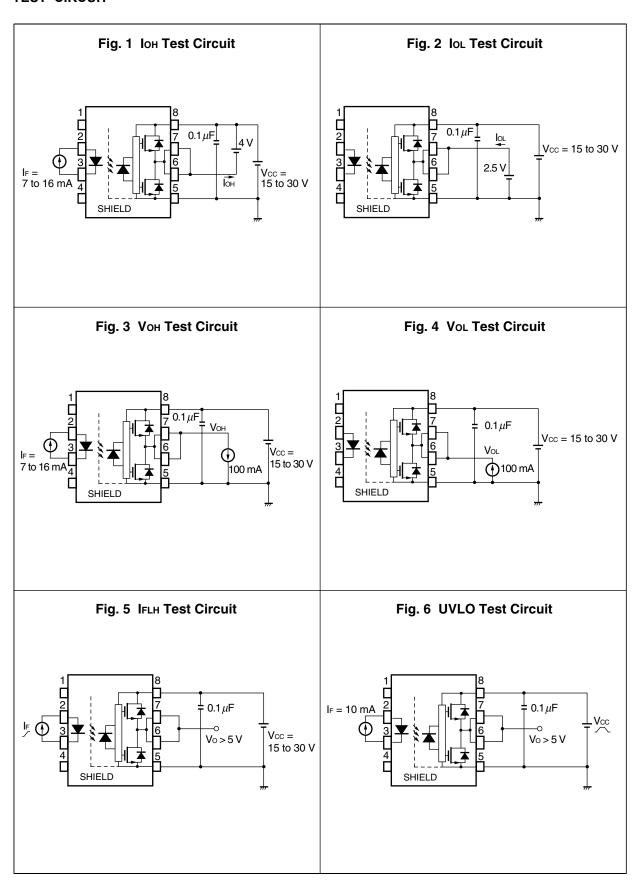
(VEE = GND, unless otherwise specified and refer to RECOMMENDED OPERATING CONDITIONS)

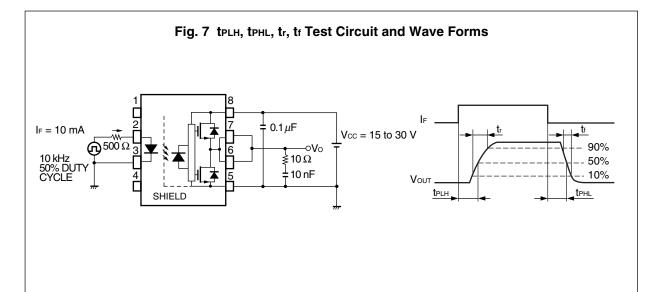
Parameter	Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit
Propagation Delay Time $(L \rightarrow H)$	t PLH	$R_g = 10 \Omega$, $C_g = 10 nF$, $f = 10 kHz$,		0.07	0.25	μs
Propagation Delay Time $(H \rightarrow L)$	t PHL	Duty Cycle = 50% ^{*2} , I _F = 10 mA		0.10	0.25	μs
Pulse Width Distortion (PWD)	tphl-tplh			0.03	0.1	μs
Propagation Delay Time (Difference Between Any Two Products)	t рнц— t рцн		-0.1		0.1	μs
Rise Time	t r			50		ns
Fall Time	t f			50		ns
UVLO (Turn On Delay)	tuvlo on	Vo > 5 V, I _F = 10 mA		0.8		μs
UVLO (Turn Off Delay)	tuvlo off	Vo < 5 V, I _F = 10 mA		0.6		μs
Common Mode Transient Immunity at High Level Output	[СМн]	T _A = 25°C, I _F = 10 to 16 mA, V _{CC} = 30 V, V _{O (MIN.)} = 26 V, V _{CM} = 1.5 kV	25			kV/μs
Common Mode Transient Immunity at Low Level Output	CM _L	T _A = 25°C, I _F = 0 mA, V _{CC} = 30 V, V _{O (MAX.)} = 1 V, V _{CM} = 1.5 kV	25			kV/μs

^{*1} Typical values at $T_A = 25^{\circ}C$.

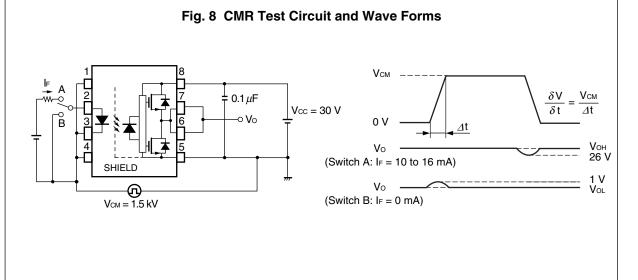
^{*2} This load condition is equivalent to the IGBT load at 1 200 V/75 A.

TEST CIRCUIT

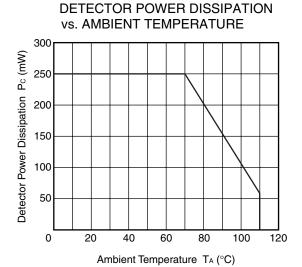




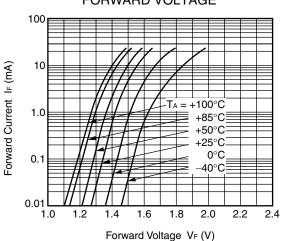
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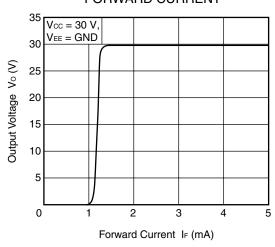
<R> TYPICAL CHARACTERISTICS (T_A = 25°C, unless otherwise specified)



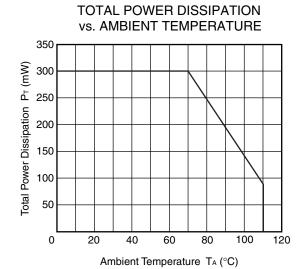
FORWARD CURRENT vs. FORWARD VOLTAGE



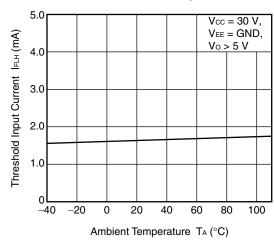
OUTPUT VOLTAGE vs. FORWARD CURRENT



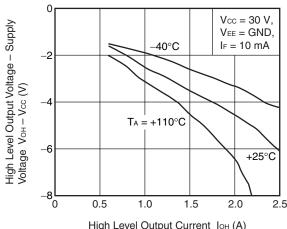
Remark The graphs indicate nominal characteristics.



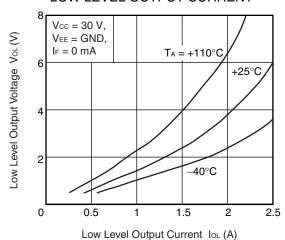
THRESHOLD INPUT CURRENT vs. AMBIENT TEMPERATURE



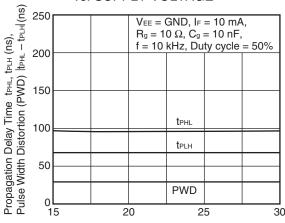
HIGH LEVEL OUTPUT VOLTAGE - SUPPLY VOLTAGE vs. HIGH LEVEL OUTPUT CURRENT



LOW LEVEL OUTPUT VOLTAGE vs. LOW LEVEL OUTPUT CURRENT

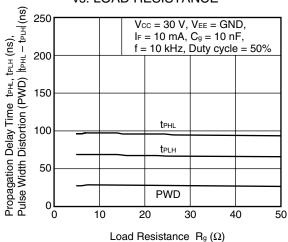


PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. SUPPLY VOLTAGE



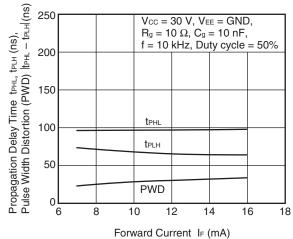
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. LOAD RESISTANCE

Supply Voltage Vcc (V)

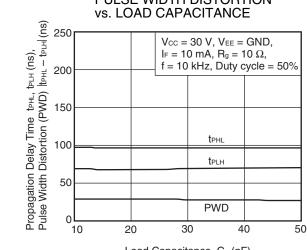


Remark The graphs indicate nominal characteristics.

PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. FORWARD CURRENT

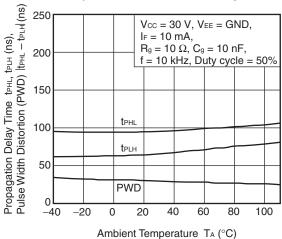


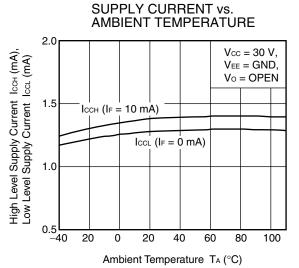
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. LOAD CAPACITANCE



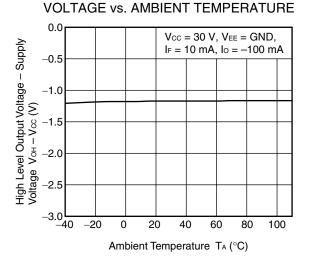
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. AMBIENT TEMPERATURE

Load Capacitance Cg (nF)

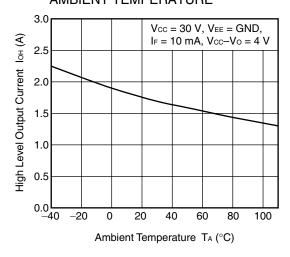




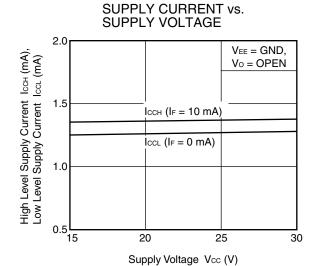
HIGH LEVEL OUTPUT VOLTAGE – SUPPLY



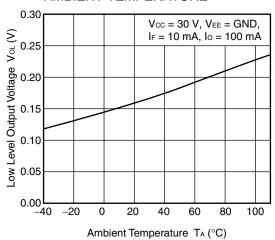
HIGH LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE



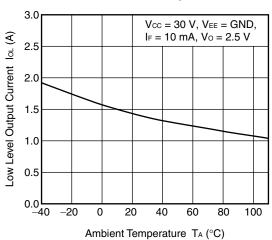
Remark The graphs indicate nominal characteristics.



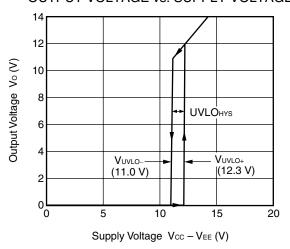
LOW LEVEL OUTPUT VOLTAGE vs. AMBIENT TEMPERATURE



LOW LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE

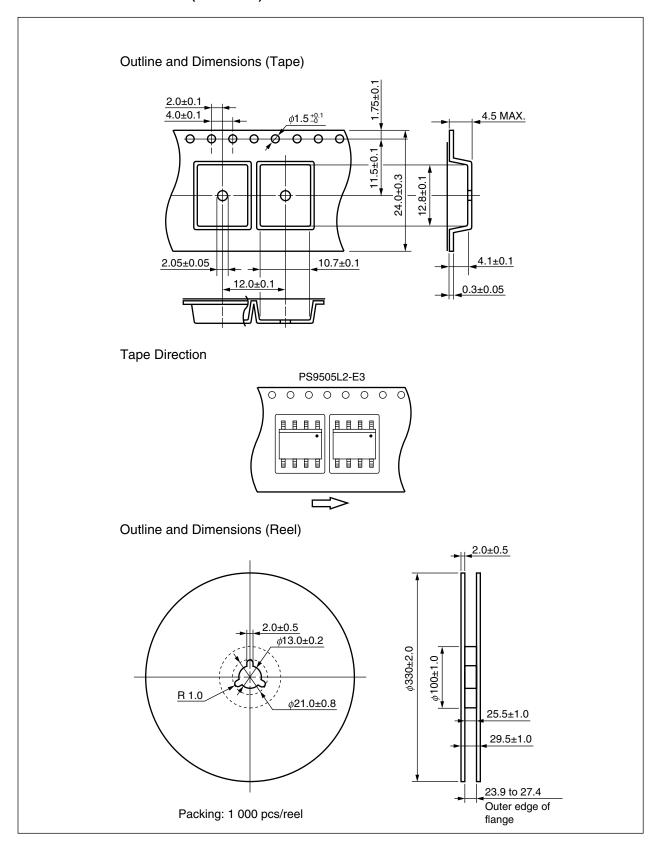


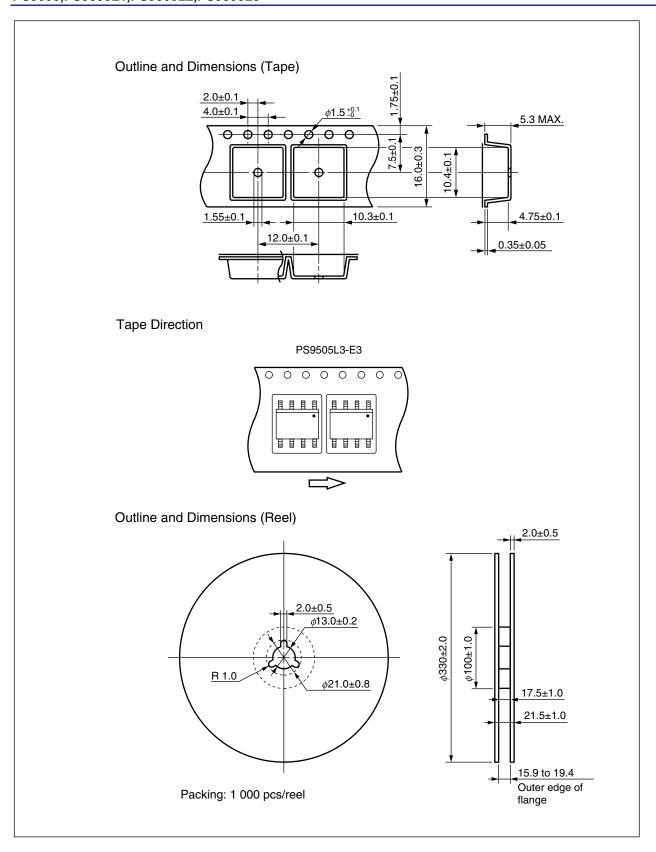
OUTPUT VOLTAGE vs. SUPPLY VOLTAGE



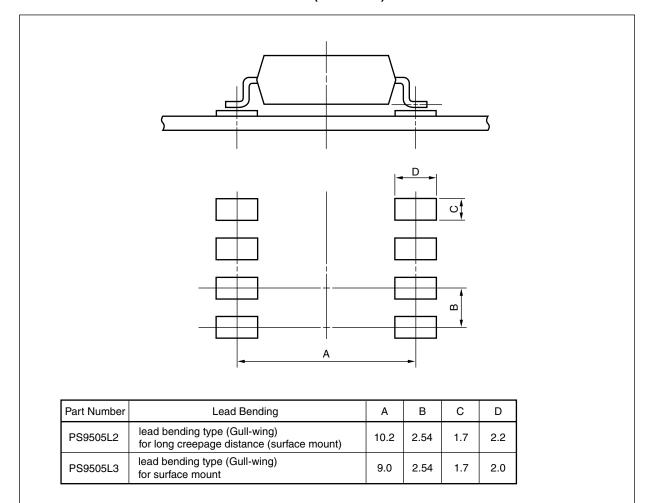
Remark The graph indicates nominal characteristics.

TAPING SPECIFICATIONS (UNIT: mm)





<R> RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)



NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

• Peak reflow temperature 260°C or below (package surface temperature)

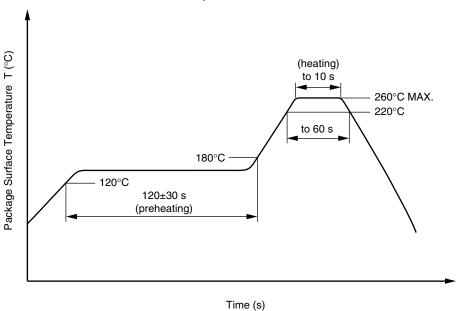
Time of peak reflow temperature
 Time of temperature higher than 220°C
 50 seconds or less
 60 seconds or less

Time to preheat temperature from 120 to 180°C 120±30 s
 Number of reflows Three

• Flux Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Wave soldering

• Temperature 260°C or below (molten solder temperature)

• Time 10 seconds or less

• Preheating conditions 120°C or below (package surface temperature)

Number of times
 One (Allowed to be dipped in solder including plastic mold portion.)

• Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content

of 0.2 Wt% is recommended.)

(3) Soldering by Soldering Iron

Peak Temperature (lead part temperature) 350°C or below
 Time (each pins) 3 seconds or less

Flux
 Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt% is recommended.)

(a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead

(4) Cautions

Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

USAGE CAUTIONS

- 1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
- 2. Board designing
 - (1) By-pass capacitor of more than 0.1 μ F is used between Vcc and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
 - (2) When designing the printed wiring board, ensure that the pattern of the IGBT collectors/emitters is not too close to the input block pattern of the photocoupler.
 - If the pattern is too close to the input block and coupling occurs, a sudden fluctuation in the voltage on the IGBT output side might affect the photocoupler's LED input, leading to malfunction or degradation of characteristics. (If the pattern needs to be close to the input block, to prevent the LED from lighting during the off state due to the abovementioned coupling, design the input-side circuit so that the bias of the LED is reversed, within the range of the recommended operating conditions, and be sure to thoroughly evaluate operation.)
 - (3) Pins 1, 4 (which is an NC*1 pin) can either be connected directly to the GND pin on the LED side or left open. Unconnected pins should not be used as a bypass for signals or for any other similar purpose because this may degrade the internal noise environment of the device.
 - *1 NC: Non-Connection (No Connection)
- 3. Make sure the rise/fall time of the forward current is 0.5 μ s or less.
- **4.** In order to avoid malfunctions, make sure the rise/fall slope of the supply voltage is $3 \text{ V}/\mu\text{s}$ or less.
- **5.** Avoid storage at a high temperature and high humidity.



<R> SPECIFICATION OF VDE MARKS LICENSE DOCUMENT

Parameter	Symbol	Spec.	Unit
Climatic test class (IEC 60068-1/DIN EN 60068-1)		40/110/21	
Dielectric strength maximum operating isolation voltage Test voltage (partial discharge test, procedure a for type test and random test) $U_{pr} = 1.6 \times U_{\text{IORM}}, P_{\text{d}} < 5 \text{pC}$	UIORM Upr	1 130 1 808	V _{peak} V _{peak}
Test voltage (partial discharge test, procedure b for all devices) $U_{pr}=1.875\times U_{IORM},\ P_d<5\ pC$	Upr	2 119	V_{peak}
Highest permissible overvoltage	Utr	8 000	Vpeak
Degree of pollution (DIN EN 60664-1 VDE0110 Part 1)		2	
Comparative tracking index (IEC 60112/DIN EN 60112 (VDE 0303 Part 11))	СТІ	175	
Material group (DIN EN 60664-1 VDE0110 Part 1)		III a	
Storage temperature range	T _{stg}	-55 to +125	°C
Operating temperature range	TA	-40 to +110	°C
Isolation resistance, minimum value V _{IO} = 500 V dc at T _A = 25°C V _{IO} = 500 V dc at T _A MAX. at least 100°C	Ris MIN. Ris MIN.	10 ¹² 10 ¹¹	Ω Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve) Package temperature	Tsi	175	°C
Current (input current I _F , Psi = 0) Power (output or total power dissipation) Isolation resistance	lsi Psi	400 700	mA mW
V _{IO} = 500 V dc at T _A = Tsi	Ris MIN.	10 ⁹	Ω

Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
 - Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
- 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.

Revision History

PS9505,PS9505L1,PS9505L2,PS9505L3 Data Sheet

		Description		
Rev.	Date	Page	Summary	
0.01	May 12, 2010	_	First Edition issued	
1.00	Jan 06, 2012	Throughout	Preliminary Data Sheet -> Data Sheet	
		Throughout	Safety standards approved	
		p.1	Addition of Pb-Free product	
		p.4	Modification of MARKING EXAMPLE	
		p.5	Addition of ORDERING INFORMATION	
		p.6	Modification of ELECTRICAL CHARACTERISTICS	
		p.7	Modification of SWITCHING CHARACTERISTICS	
		p.9	Modification of TEST CIRCUIT	
		pp.10 to 13	Addition of TYPICAL CHARACTERISTICS	
		p.16	Modification of RECOMMENDED MOUNT PAD DIMENSIONS	
		p.18	Modification of USAGE CAUTIONS 2. (2)	
		p.19	Addition of SPECIFICATION OF VDE MARKS LICENSE DOCUMENT	

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